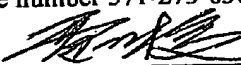


JAN 30 2006

## Certificate of Facsimile Transmission

I hereby certify that the attached Transmittal (1 page), Response to the Office Action dated July 12, 2005 and Amendment not responsive mailed December 29, 2005(12 pages) are submitted to the U.S. Patent and Trademark Office via facsimile number 571-273-8300 on the date shown below. (Total 13 pages).

  
Li Mei Vermilya

Date: January 30, 2006

PATENT APPLICATION  
Attorney Docket No.: 9898-326  
Client Ref. No.: SS-20348-US

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Kyoung-Woo LEE, et al.

Serial No.: 10/688,077 Examiner: Guerrero, Maria F.

Filed: October 16, 2003 Group Art Unit: 2822

Confirmation No.: 8142

For: INTEGRATED CIRCUIT CAPACITOR STRUCTURE

Mail Stop Amendment  
Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Responsive to the Office Action dated July 12, 2005 and Amendment not responsive mailed December 29, 2005, enclosed is an amendment in the above-identified application.

The fee has been calculated as shown below.

CLAIMS AS AMENDED					
For:	Number After Amendment	Previous Number	Extra	Rate	Additional Fee
Total Claims	22	22	0	x \$50 =	\$0
Independent Claims	3	3	0	x \$200 =	\$0
TOTAL ADDITIONAL FEE FOR THIS AMENDMENT					\$0

\*greater of twenty (20) or number for which fee has been paid

\*\*greater of three (3) or number for which fee has been paid

☒ Any deficiency or overpayment should be charged or credited to deposit account number 13-1703.

Customer No. 20575

Respectfully submitted,  
MARGER JOHNSON & McCOLLOM, P.C.

  
Hosoon Lee, Reg. No. 56,737

MARGER JOHNSON & McCOLLOM, P.C.  
210 SW Morrison Street, Suite 400  
Portland, OR 97204  
(503) 222-3613

JAN 30 2006

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## SUPPLEMENTAL AMENDMENT

Responsive to the Office Action, Paper No. 20050708, dated July 12, 2005, and the USPTO communication mailed on December 29, 2005, please amend the application as follows.

**Response to the USPTO communication mailed on December 29, 2005 begins on page 2.**

**Amendments to the Specification begin on page 3 of this paper.**

**Amendments to the Claims are reflected in the listing of claims which begins on page 4 of this paper.**

**Remarks/Arguments begin on page 8 of this paper.**

**AMENDMENT NOT RESPONSIVE**

The following is also repeated in the Remarks/Arguments that begins on page 8 of this paper.

Applicants now respond to the USPTO communication mailed on December 29, 2005.

For an illustrative example, claim 1, reading on the embodiment shown in FIG. 5, follows;

A method of manufacturing an MIM capacitor, which includes a lower electrode 120, a first wiring layer 112 that is located below or in a same level with the lower electrode 120 and is insulated from the lower electrode 120, and an upper electrode 140 that overlaps with the lower electrode 120 and contacts the first wiring layer through a contact hole C/H1 in a dielectric layer 130 that is between the upper electrode 140 and the lower electrode 120, the method comprising:

forming the dielectric layer 130 on the entire surface of a substrate on which the lower electrode 120 and the first wiring layer 112 are formed;

patterning the dielectric layer 130 to form the contact hole C/H1 through which the surface of the first wiring layer 112 is exposed; and

forming the upper electrode 140 comprising a material to contact the first wiring layer 112 through the contact hole C/H1.

The examiner says that it is unclear how the surface of the first wiring layer 112 is exposed when the first wiring layer 112 is located below the lower electrode 120 because the claim recited that the first wiring layer 112 is insulated from the lower electrode 120. Applicant respectfully points out that the lower electrode 120, as in the embodiment of FIG. 5, extends horizontally only a limited distance, short of where the contact hole C/H1 penetrates the dielectric layer 130. Because the contact hole C/H1 penetrates the dielectric layer 130 directly over the first wiring layer 112, in this embodiment, the surface of the first wiring layer 112 is exposed even though the first wiring layer 112 is located below the lower electrode 120.

The Examiner is encouraged to telephone applicant's representative if there are any questions or recommendations.